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Abstract of the Disclosure

A method and apparatus for measuring essentially real-time concentrations of gaseous contaminants exiting a semiconductor processing chamber. A small volume of exhaust gases from the processing chamber is drawn through one or more microsensors. The microsensors are selected to measure gaseous contaminants such as moisture, oxygen, carbon dioxide, or combinations thereof. *In situ* monitors comprising a thin film sensor are preferred. The *in situ* monitors preferably can be selectively communicated with the exhaust gases from the processing chamber and process gases which bypass the processing chamber.

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